VRW0;< ṂṂ Ŀ SQS ӕ Ṁ ɥ s Ⅱ ⅂ Silicon PNP transistor in a SOT-89 Plastic Package.

` Ɯ Ͻ я ϫ ı ώ̤ ᵶ ˧ ớ Ḃ ı ټ ⁼ я ں Ḩ ı љ EU5VG4;<;T Ӣ ´ ı ˨ ᵀ DHF0T434 ‰´ ϫ ˡ ˛ ớ ⌊ ∂ ı ŋ̇ ғ ᵝ

High breakdown voltage, good h_{FE} linearity, low $V_{CE(sat)}$, complements the BR2SD1898Q, Qualified to AEC-Q101 Standards for High Reliability, HF Product.

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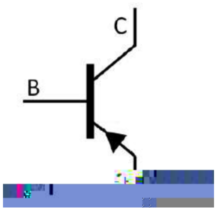
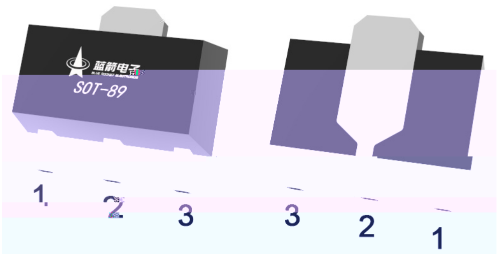
General power amplifier applications, Meet the stringent requirements of automotive applications.

/ Equivalent Circuit





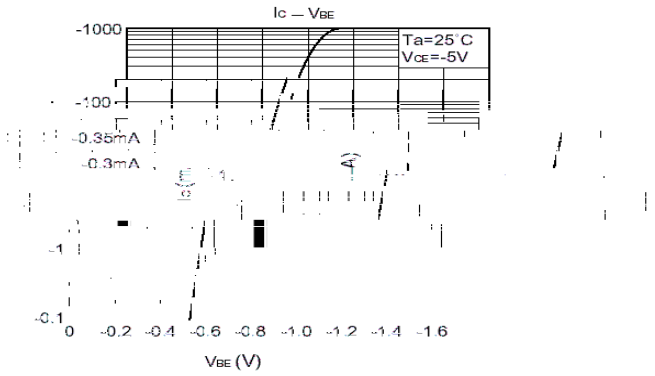
PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

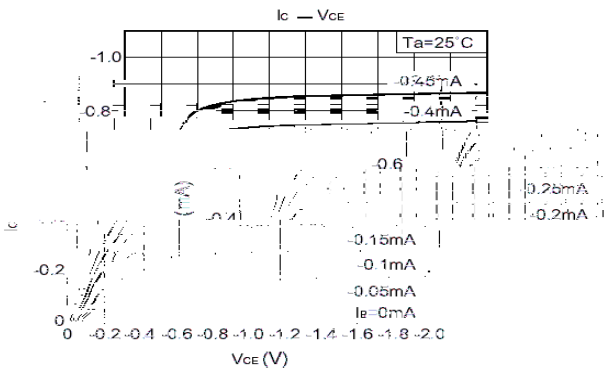
v ¨Q Parameter	↑ N Symbol	¨Q Ö Rating	D Ц Unit
Collector to Base Voltage	V_{CBO}	-80	V
Collector to Emitter Voltage	V_{CEO}	-80	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current-Continuous	I_C	-1.0	A
Collector Current-Continuous(Pulse)	*I_{CP}	-2.0	A
Collector Power Dissipation	**P_C	0.5	W
	*P_C	2.0	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

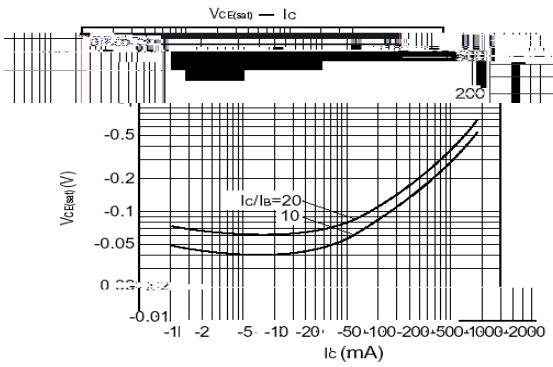
*Single pulse Pw=100ms ǐ˙ ╜ : ı ǐ Ķ 100ms
**mounted on 40×40×0.7mm ceramic board Ɛ̂ 40×40×0.7m ▒ i

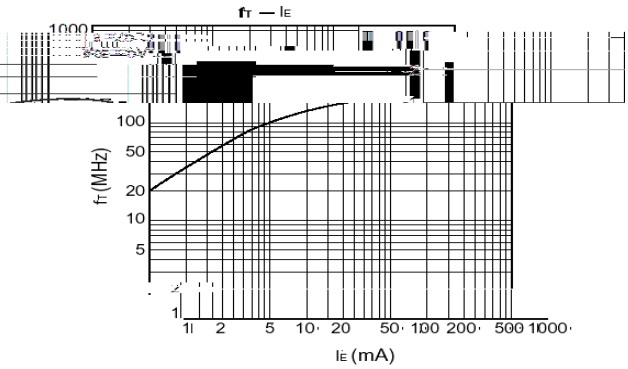
v ¨Q Parameter	↑ N Symbol	╜ :† ţ Test Conditions	ѡ ņ Ö Min	Ɛ ʒ Ö Typ	ѡ ² Ö Max	D Ц Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=-50μA I_E=0	-80			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-1.0mA I_B=0	-80			V

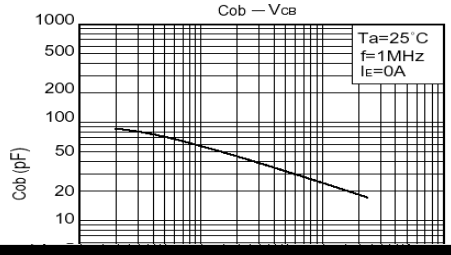
/ Electrical Characteristic Curve

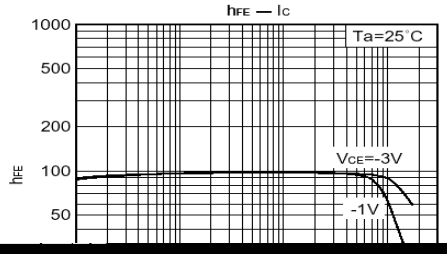




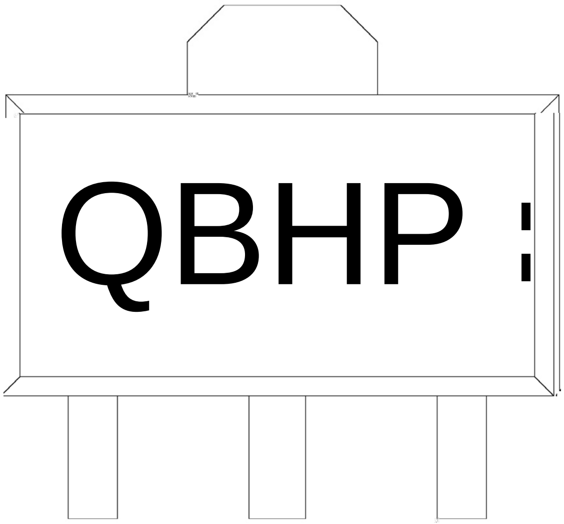








/ Marking Instructions



ب ˝ χ

T χ ꞃ ∩ ج ṅ ғ ᵝ ‰ ∜

BH χ ꞃ ვ ᴺ ᥰ

P χ ꞃ h_{FE} ˂ ⁶ ᥰ

-- χ ꞃ ꞁ ғ ῆ ᴺ ᥰ ı ꞓ ꞁ ғ ῆ ᴺ ψ ק

Note:

Q:	Automobile halogen-free product Code
BH:	Product Type
P χ	h_{FE} Classifications Symbol
**:	Lot No. Code, code change with Lot No

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)

ب ˝ χ

1 ꞁ ♬ □ ŷ 150 Ḱ 200 ƚ ι ˋH ڗ 60 Ḱ 120sec;

2 Š Ö □ ŷ 255 ° 5 ƚ ι ˋH ڗ ˋY ﾊ ᄩ 5 ° 0.5sec;

3 ì ˙ ˥ ˛ ɔ ៚ ŷ ᄩ 2 Ḱ 10 ƚ /sec.

Note:

1.Preheating:150~200 ƚ , Time:60~120sec.

2.Peak Temp.:255 ° 5 ƚ , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ƚ /sec.

/ Resistance to Soldering Heat Test Conditions

□ ŷ χ 260 ° 5 ƚ ˋH ڗ χ 10 ° 1 sec.

Temp.:260±5 Time:10±1 sec